



RF PLL Frequency Synthesizers

ADF4110/ADF4111/ADF4112/ADF4113

FEATURES

ADF4110: 550 MHz

ADF4111: 1.2 GHz

ADF4112: 3.0 GHz

ADF4113: 4.0 GHz

2.7 V to 5.5 V Power Supply

Separate Charge Pump Supply (V_P) Allows Extended Tuning Voltage in 3 V Systems

Programmable Dual-Modulus Prescaler 8/9, 16/17, 32/33, 64/65

Programmable Charge Pump Currents

Programmable Antibacklash Pulsewidth

3-Wire Serial Interface

Analog and Digital Lock Detect

Hardware and Software Power-Down Mode

APPLICATIONS

Base Stations for Wireless Radio (GSM, PCS, DCS, CDMA, WCDMA)

Wireless Handsets (GSM, PCS, DCS, CDMA, WCDMA)

Wireless LANS

Communications Test Equipment

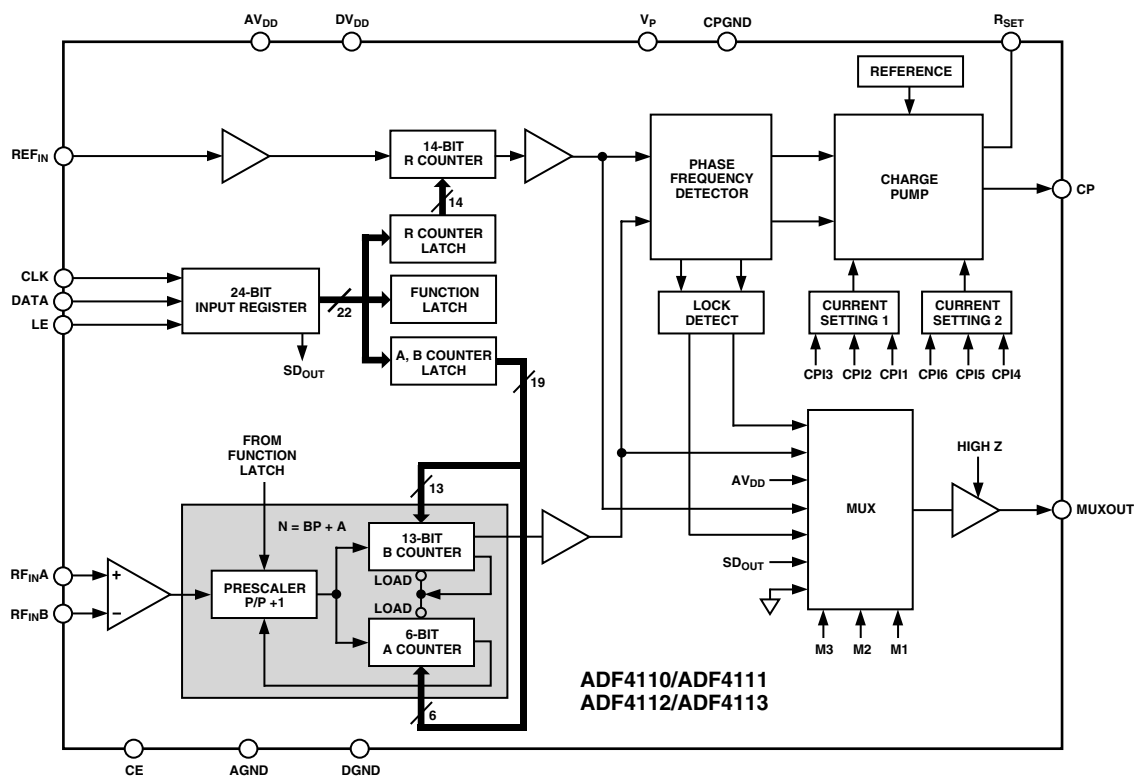
CATV Equipment

GENERAL DESCRIPTION

The ADF4110 family of frequency synthesizers can be used to implement local oscillators in the upconversion and down-conversion sections of wireless receivers and transmitters. They consist of a low-noise digital PFD (phase frequency detector), a precision charge pump, a programmable reference divider, programmable A and B counters, and a dual-modulus prescaler ($P/P + 1$). The A (6-bit) and B (13-bit) counters, in conjunction with the dual-modulus prescaler ($P/P + 1$), implement an N divider ($N = BP + A$). In addition, the 14-bit reference counter (R counter) allows selectable REF frequencies at the PFD input. A complete phase-locked loop (PLL) can be implemented if the synthesizer is used with an external loop filter and voltage controlled oscillator (VCO).

Control of all the on-chip registers is via a simple 3-wire interface. The devices operate with a power supply ranging from 2.7 V to 5.5 V and can be powered down when not in use.

FUNCTIONAL BLOCK DIAGRAM



REV. B

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ADF4110/ADF4111/ADF4112/ADF4113—SPECIFICATIONS¹

($AV_{DD} = DV_{DD} = 3\text{ V} \pm 10\%$, $5\text{ V} \pm 10\%$; $AV_{DD} \leq V_P \leq 6.0\text{ V}$; $AGND = DGND = CPGND = 0\text{ V}$; $R_{SET} = 4.7\text{ k}\Omega$; dBm referred to $50\text{ }\Omega$; $T_A = T_{MIN}$ to T_{MAX} , unless otherwise noted.)

Parameter	B Version	B Chips ²	Unit	Test Conditions/Comments
RF CHARACTERISTICS (3 V)				
RF Input Frequency				See Figure 3 for input circuit. Use a square wave for lower frequencies, below the minimum level stated. Input Level = -10 dBm
ADF4110	80/550	80/550	MHz min/max	
ADF4110	50/550	50/550	MHz min/max	
ADF4111	0.08/1.2	0.08/1.2	GHz min/max	
ADF4112	0.2/3.0	0.2/3.0	GHz min/max	
ADF4112	0.1/3.0	0.1/3.0	GHz min/max	Input Level = -10 dBm
ADF4113	0.2/3.7	0.2/3.7	GHz min/max	Input Level = -10 dBm
RF Input Sensitivity	-15/0	-15/0	dBm min/max	
Maximum Allowable Prescaler Output Frequency ³	165	165	MHz max	
RF CHARACTERISTICS (5 V)				
RF Input Frequency				Use a square wave for lower frequencies, below the minimum level stated.
ADF4110	80/550	80/550	MHz min/max	
ADF4111	0.08/1.4	0.08/1.4	GHz min/max	
ADF4112	0.1/3.0	0.1/3.0	GHz min/max	
ADF4113	0.2/3.7	0.2/3.7	GHz min/max	
ADF4113	0.2/4.0	0.2/4.0	GHz min/max	Input Level = -5 dBm
RF Input Sensitivity	-10/0	-10/0	dBm min/max	
Maximum Allowable Prescaler Output Frequency ³	200	200	MHz max	
REFIN CHARACTERISTICS				
REFIN Input Frequency	5/104	5/104	MHz min/max	For $f < 5\text{ MHz}$, use dc-coupled square wave, (0 to V_{DD}).
Reference Input Sensitivity ⁴	-5	-5	dBm min	AC-Coupled. When dc-coupled: 0 to V_{DD} max (CMOS Compatible)
REFIN Input Capacitance	10	10	pF max	
REFIN Input Current	± 100	± 100	μA max	
PHASE DETECTOR				
Phase Detector Frequency ⁵	55	55	MHz max	
CHARGE PUMP				
I_{CP} Sink/Source				Programmable (see Table V)
High Value	5	5	mA typ	With $R_{SET} = 4.7\text{ k}\Omega$
Low Value	625	625	μA typ	
Absolute Accuracy	2.5	2.5	% typ	With $R_{SET} = 4.7\text{ k}\Omega$
R_{SET} Range	2.7/10	2.7/10	k Ω typ	See Table V
I_{CP} 3-State Leakage Current	1	1	nA typ	
Sink and Source Current Matching	2	2	% typ	$0.5\text{ V} \leq V_{CP} \leq V_P - 0.5$
I_{CP} vs. V_{CP}	1.5	1.5	% typ	$0.5\text{ V} \leq V_{CP} \leq V_P - 0.5$
I_{CP} vs. Temperature	2	2	% typ	$V_{CP} = V_P/2$
LOGIC INPUTS				
V_{INH} , Input High Voltage	$0.8 \times DV_{DD}$	$0.8 \times DV_{DD}$	V min	
V_{INL} , Input Low Voltage	$0.2 \times DV_{DD}$	$0.2 \times DV_{DD}$	V max	
I_{INH}/I_{INL} , Input Current	± 1	± 1	μA max	
C_{IN} , Input Capacitance	10	10	pF max	
LOGIC OUTPUTS				
V_{OH} , Output High Voltage	$DV_{DD} - 0.4$	$DV_{DD} - 0.4$	V min	$I_{OH} = 500\text{ }\mu\text{A}$
V_{OL} , Output Low Voltage	0.4	0.4	V max	$I_{OL} = 500\text{ }\mu\text{A}$
POWER SUPPLIES				
AV_{DD}	2.7/5.5	2.7/5.5	V min/V max	
DV_{DD}	AV_{DD}	AV_{DD}		
V_P	$AV_{DD}/6.0$	$AV_{DD}/6.0$	V min/V max	$AV_{DD} \leq V_P \leq 6.0\text{ V}$
I_{DD} ⁶ ($AI_{DD} + DI_{DD}$)				See TPCs 21a and 21b
ADF4110	5.5	4.5	mA max	4.5 mA typical
ADF4111	5.5	4.5	mA max	4.5 mA typical
ADF4112	7.5	6.5	mA max	6.5 mA typical
ADF4113	11	8.5	mA max	8.5 mA typical
I_P	0.5	0.5	mA max	$T_A = 25^\circ\text{C}$
Low Power Sleep Mode	1	1	μA typ	

ADF4110/ADF4111/ADF4112/ADF4113

Parameter	B Version	B Chips ²	Unit	Test Conditions/Comments
NOISE CHARACTERISTICS				
ADF4113 Phase Noise Floor ⁷	–171	–171	dBc/Hz typ	@ 25 kHz PFD Frequency
	–164	–164	dBc/Hz typ	@ 200 kHz PFD Frequency
Phase Noise Performance ⁸				@ VCO Output
ADF4110: 540 MHz Output ⁹	–91	–91	dBc/Hz typ	@ 1 kHz Offset and 200 kHz PFD Frequency
ADF4111: 900 MHz Output ¹⁰	–87	–87	dBc/Hz typ	@ 1 kHz Offset and 200 kHz PFD Frequency
ADF4112: 900 MHz Output ¹⁰	–90	–90	dBc/Hz typ	@ 1 kHz Offset and 200 kHz PFD Frequency
ADF4113: 900 MHz Output ¹⁰	–91	–91	dBc/Hz typ	@ 1 kHz Offset and 200 kHz PFD Frequency
ADF4111: 836 MHz Output ¹¹	–78	–78	dBc/Hz typ	@ 300 Hz Offset and 30 kHz PFD Frequency
ADF4112: 1750 MHz Output ¹²	–86	–86	dBc/Hz typ	@ 1 kHz Offset and 200 kHz PFD Frequency
ADF4112: 1750 MHz Output ¹³	–66	–66	dBc/Hz typ	@ 200 Hz Offset and 10 kHz PFD Frequency
ADF4112: 1960 MHz Output ¹⁴	–84	–84	dBc/Hz typ	@ 1 kHz Offset and 200 kHz PFD Frequency
ADF4113: 1960 MHz Output ¹⁴	–85	–85	dBc/Hz typ	@ 1 kHz Offset and 200 kHz PFD Frequency
ADF4113: 3100 MHz Output ¹⁵	–86	–86	dBc/Hz typ	@ 1 kHz Offset and 1 MHz PFD Frequency
Spurious Signals				
ADF4110: 540 MHz Output ⁹	–97/–106	–97/–106	dBc typ	@ 200 kHz/400 kHz and 200 kHz PFD Frequency
ADF4111: 900 MHz Output ¹⁰	–98/–110	–98/–110	dBc typ	@ 200 kHz/400 kHz and 200 kHz PFD Frequency
ADF4112: 900 MHz Output ¹⁰	–91/–100	–91/–100	dBc typ	@ 200 kHz/400 kHz and 200 kHz PFD Frequency
ADF4113: 900 MHz Output ¹⁰	–100/–110	–100/–110	dBc typ	@ 200 kHz/400 kHz and 200 kHz PFD Frequency
ADF4111: 836 MHz Output ¹¹	–81/–84	–81/–84	dBc typ	@ 30 kHz/60 kHz and 30 kHz PFD Frequency
ADF4112: 1750 MHz Output ¹²	–88/–90	–88/–90	dBc typ	@ 200 kHz/400 kHz and 200 kHz PFD Frequency
ADF4112: 1750 MHz Output ¹³	–65/–73	–65/–73	dBc typ	@ 10 kHz/20 kHz and 10 kHz PFD Frequency
ADF4112: 1960 MHz Output ¹⁴	–80/–84	–80/–84	dBc typ	@ 200 kHz/400 kHz and 200 kHz PFD Frequency
ADF4113: 1960 MHz Output ¹⁴	–80/–84	–80/–84	dBc typ	@ 200 kHz/400 kHz and 200 kHz PFD Frequency
ADF4113: 3100 MHz Output ¹⁵	–80/–82	–82/–82	dBc typ	@ 1 MHz/2 MHz and 1 MHz PFD Frequency

NOTES

¹Operating temperature range is as follows: B Version: –40°C to +85°C.

²The B Chip specifications are given as typical values.

³This is the maximum operating frequency of the CMOS counters. The prescaler value should be chosen to ensure that the RF input is divided down to a frequency that is less than this value.

⁴AV_{DD} = DV_{DD} = 3 V; for AV_{DD} = DV_{DD} = 5 V, use CMOS compatible levels.

⁵Guaranteed by design.

⁶T_A = 25°C; AV_{DD} = DV_{DD} = 3 V; P = 16; SYNC = 0; DLY = 0; RF_{IN} for ADF4110 = 540 MHz; RF_{IN} for ADF4111, ADF4112, ADF4113 = 900 MHz.

⁷The synthesizer phase noise floor is estimated by measuring the in-band phase noise at the output of the VCO and subtracting 20 logN (where N is the N divider value).

⁸The phase noise is measured with the EVAL-ADF411XEB1 Evaluation Board and the HP8562E Spectrum Analyzer. The spectrum analyzer provides the REFIN for the synthesizer (f_{REFOUT} = 10 MHz @ 0 dBm). SYNC = 0; DLY = 0 (See Table III).

⁹f_{REFIN} = 10 MHz; f_{PFD} = 200 kHz; Offset frequency = 1 kHz; f_{RF} = 540 MHz; N = 2700; Loop B/W = 20 kHz.

¹⁰f_{REFIN} = 10 MHz; f_{PFD} = 200 kHz; Offset frequency = 1 kHz; f_{RF} = 900 MHz; N = 4500; Loop B/W = 20 kHz.

¹¹f_{REFIN} = 10 MHz; f_{PFD} = 30 kHz; Offset frequency = 300 Hz; f_{RF} = 836 MHz; N = 27867; Loop B/W = 3 kHz.

¹²f_{REFIN} = 10 MHz; f_{PFD} = 200 kHz; Offset frequency = 1 kHz; f_{RF} = 1750 MHz; N = 8750; Loop B/W = 20 kHz.

¹³f_{REFIN} = 10 MHz; f_{PFD} = 10 kHz; Offset frequency = 200 Hz; f_{RF} = 1750 MHz; N = 175000; Loop B/W = 1 kHz.

¹⁴f_{REFIN} = 10 MHz; f_{PFD} = 200 kHz; Offset frequency = 1 kHz; f_{RF} = 1960 MHz; N = 9800; Loop B/W = 20 kHz.

¹⁵f_{REFIN} = 10 MHz; f_{PFD} = 1 MHz; Offset frequency = 1 kHz; f_{RF} = 3100 MHz; N = 3100; Loop B/W = 20 kHz.

Specifications subject to change without notice.

TIMING CHARACTERISTICS* (AV_{DD} = DV_{DD} = 3 V ± 10%, 5 V ± 10%; AV_{DD} ≤ V_P ≤ 6 V; AGND = DGND = CPGND = 0 V; R_{SET} = 4.7 kΩ; T_A = T_{MIN} to T_{MAX}, unless otherwise noted.)

Parameter	Limit at T _{MIN} to T _{MAX} (B Version)	Unit	Test Conditions/Comments
t ₁	10	ns min	DATA to CLOCK Setup Time
t ₂	10	ns min	DATA to CLOCK Hold Time
t ₃	25	ns min	CLOCK High Duration
t ₄	25	ns min	CLOCK Low Duration
t ₅	10	ns min	CLOCK to LE Setup Time
t ₆	20	ns min	LE Pulswidth

*Guaranteed by design but not production tested.

Specifications subject to change without notice.

ADF4110/ADF4111/ADF4112/ADF4113

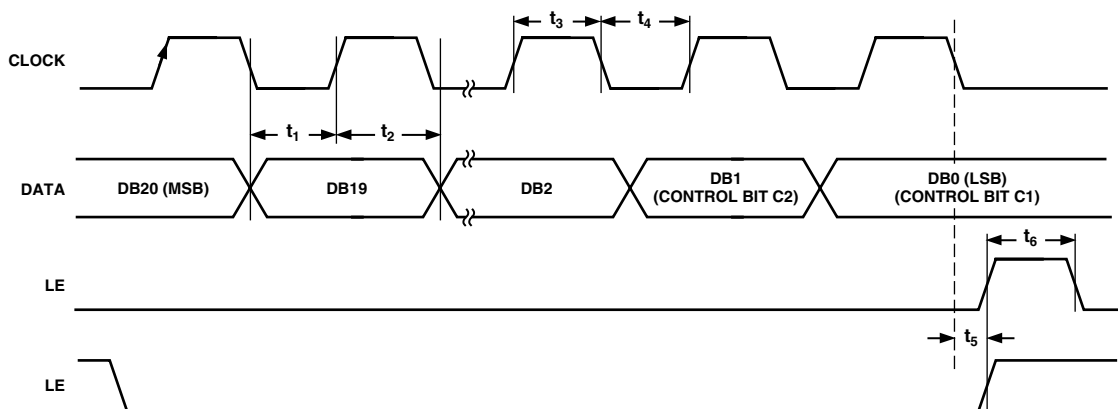


Figure 1. Timing Diagram

ABSOLUTE MAXIMUM RATINGS^{1, 2}

(T_A = 25°C, unless otherwise noted.)

AV _{DD} to GND ³	–0.3 V to +7 V
AV _{DD} to DV _{DD}	–0.3 V to +0.3 V
V _P to GND	–0.3 V to +7 V
V _P to AV _{DD}	–0.3 V to +5.5 V
Digital I/O Voltage to GND	–0.3 V to V _{DD} + 0.3 V
Analog I/O Voltage to GND	–0.3 V to V _P + 0.3 V
REF _{IN} , RF _{IN} A, RF _{IN} B to GND	–0.3 V to V _{DD} + 0.3 V
RF _{IN} A to RF _{IN} B	±320 mV
Operating Temperature Range	
Industrial (B Version)	–40°C to +85°C
Storage Temperature Range	–65°C to +150°C
Maximum Junction Temperature	150°C
TSSOP θ _{JA} Thermal Impedance	150.4°C/W

LFCSP θ_{JA} Thermal Impedance

(Paddle Soldered) 122°C/W

LFCSP θ_{JA} Thermal Impedance

(Paddle Not Soldered) 216°C/W

Lead Temperature, Soldering

Vapor Phase (60 sec) 215°C

Infrared (15 sec) 220°C

NOTES

¹Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

²This device is a high performance RF integrated circuit with an ESD rating of <2 kV and it is ESD sensitive. Proper precautions should be taken for handling and assembly.

³GND = AGND = DGND = 0 V.

TRANSISTOR COUNT

6425 (CMOS) and 303 (Bipolar).

ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option*
ADF4110BRU	–40°C to +85°C	Thin Shrink Small Outline Package (TSSOP)	RU-16
ADF4110BCP	–40°C to +85°C	Lead Frame Chip Scale Package (LFCSP)	CP-20
ADF4111BRU	–40°C to +85°C	Thin Shrink Small Outline Package (TSSOP)	RU-16
ADF4111BCP	–40°C to +85°C	Lead Frame Chip Scale Package (LFCSP)	CP-20
ADF4112BRU	–40°C to +85°C	Thin Shrink Small Outline Package (TSSOP)	RU-16
ADF4112BCP	–40°C to +85°C	Lead Frame Chip Scale Package (LFCSP)	CP-20
ADF4113BRU	–40°C to +85°C	Thin Shrink Small Outline Package (TSSOP)	RU-16
ADF4113BCP	–40°C to +85°C	Lead Frame Chip Scale Package (LFCSP)	CP-20
ADF4113BCHIPS	–40°C to +85°C	DICE	DICE

*Contact the factory for chip availability.

CAUTION

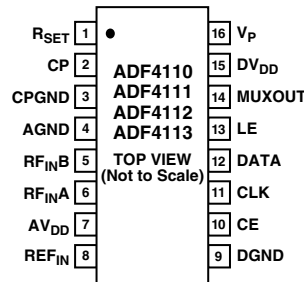
ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the ADF4110/ADF4111/ADF4112/ADF4113 features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



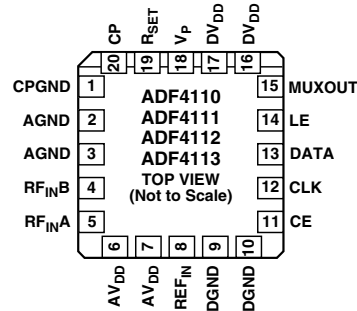
ADF4110/ADF4111/ADF4112/ADF4113

PIN CONFIGURATIONS

TSSOP



LFCSP



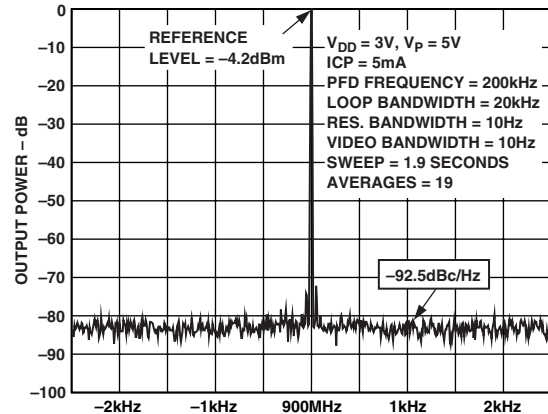
PIN FUNCTION DESCRIPTIONS

TSSOP Pin No.	LFCSP Pin No.	Mnemonic	Function
1	19	R _{SET}	Connecting a resistor between this pin and CPGND sets the maximum charge pump output current. The nominal voltage potential at the R _{SET} pin is 0.56 V. The relationship between I _{CP} and R _{SET} is $I_{CP\max} = \frac{23.5}{R_{SET}}$ So, with R _{SET} = 4.7 kΩ, I _{CPmax} = 5 mA.
2	20	CP	Charge Pump Output. When enabled, this provides ±I _{CP} to the external loop filter, which in turn drives the external VCO.
3	1	CPGND	Charge Pump Ground. This is the ground return path for the charge pump.
4	2, 3	AGND	Analog Ground. This is the ground return path of the prescaler.
5	4	RF _{INB}	Complementary Input to the RF Prescaler. This point should be decoupled to the ground plane with a small bypass capacitor, typically 100 pF. See Figure 3.
6	5	RF _{INA}	Input to the RF Prescaler. This small signal input is ac-coupled from the VCO.
7	6, 7	AV _{DD}	Analog Power Supply. This may range from 2.7 V to 5.5 V. Decoupling capacitors to the analog ground plane should be placed as close as possible to this pin. AV _{DD} must be the same value as DV _{DD} .
8	8	REF _{IN}	Reference Input. This is a CMOS input with a nominal threshold of V _{DD} /2 and an equivalent input resistance of 100 kΩ. See Figure 2. This input can be driven from a TTL or CMOS crystal oscillator or it can be ac-coupled.
9	9, 10	DGND	Digital Ground.
10	11	CE	Chip Enable. A logic low on this pin powers down the device and puts the charge pump output into three-state mode. Taking the pin high will power up the device depending on the status of the power-down bit F2.
11	12	CLK	Serial Clock Input. This serial clock is used to clock in the serial data to the registers. The data is latched into the 24-bit shift register on the CLK rising edge. This input is a high impedance CMOS input.
12	13	DATA	Serial Data Input. The serial data is loaded MSB first with the two LSBs being the control bits. This input is a high impedance CMOS input.
13	14	LE	Load Enable, CMOS Input. When LE goes high, the data stored in the shift registers is loaded into one of the four latches, the latch being selected using the control bits.
14	15	MUXOUT	This multiplexer output allows either the lock detect, the scaled RF, or the scaled reference frequency to be accessed externally.
15	16, 17	DV _{DD}	Digital Power Supply. This may range from 2.7 V to 5.5 V. Decoupling capacitors to the digital ground plane should be placed as close as possible to this pin. DV _{DD} must be the same value as AV _{DD} .
16	18	V _P	Charge Pump Power Supply. This should be greater than or equal to V _{DD} . In systems where V _{DD} is 3 V, it can be set to 6 V and used to drive a VCO with a tuning range of up to 6 V.

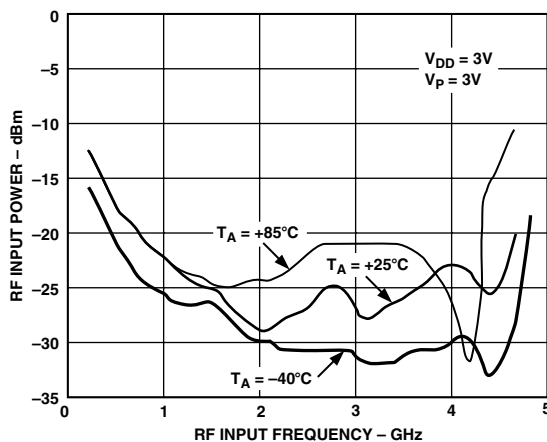
ADF4110/ADF4111/ADF4112/ADF4113—Typical Performance Characteristics

FREQ-UNIT	PARAM-TYPE	DATA-FORMAT	KEYWORD	IMPEDANCE	- OHMS
GHz	S	MA	R	50	
FREQ	MAGS11	ANGS11	FREQ	MAGS11	ANGS11
0.05	0.89207	-2.0571	1.05	0.9512	-40.134
0.10	0.8886	-4.4427	1.10	0.93458	-43.747
0.15	0.89022	-6.3212	1.15	0.94782	-44.393
0.20	0.96323	-2.1393	1.20	0.96875	-46.937
0.25	0.90566	-12.13	1.25	0.92216	-49.6
0.30	0.90307	-13.52	1.30	0.93755	-51.884
0.35	0.89318	-15.746	1.35	0.96178	-51.21
0.40	0.89806	-18.056	1.40	0.94354	-53.55
0.45	0.89565	-19.693	1.45	0.95189	-56.786
0.50	0.88538	-22.246	1.50	0.97647	-58.781
0.55	0.89699	-24.336	1.55	0.98619	-60.545
0.60	0.89927	-25.948	1.60	0.95459	-61.43
0.65	0.87797	-28.457	1.65	0.97945	-61.241
0.70	0.90765	-29.735	1.70	0.98864	-64.051
0.75	0.88526	-31.879	1.75	0.97399	-66.19
0.80	0.81267	-32.681	1.80	0.97216	-63.775
0.85	0.90357	-31.522			
0.90	0.92954	-34.222			
0.95	0.92087	-36.961			
1.00	0.93788	-39.343			

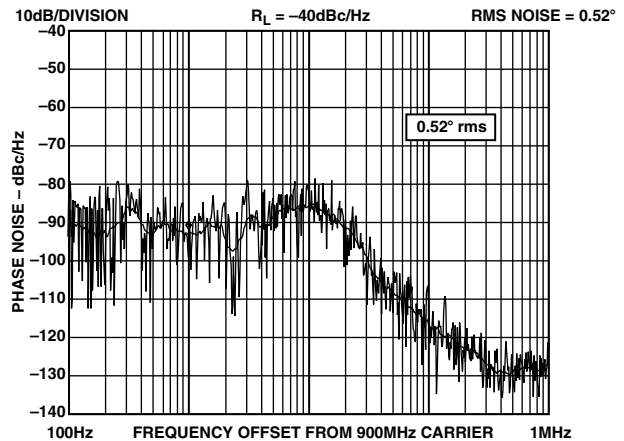
TPC 1. S-Parameter Data for the ADF4113 RF Input (Up to 1.8 GHz)



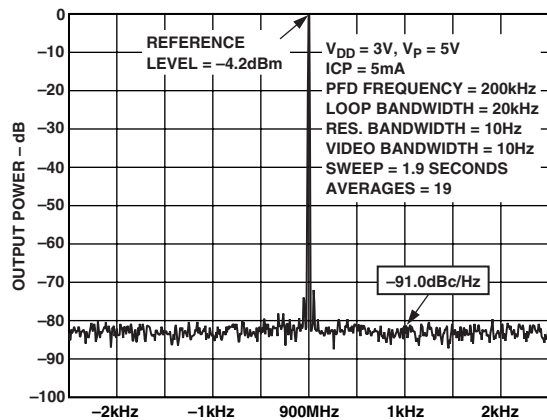
TPC 4. ADF4113 Phase Noise (900 MHz, 200 kHz, 20 kHz) with DLY and SYNC Enabled



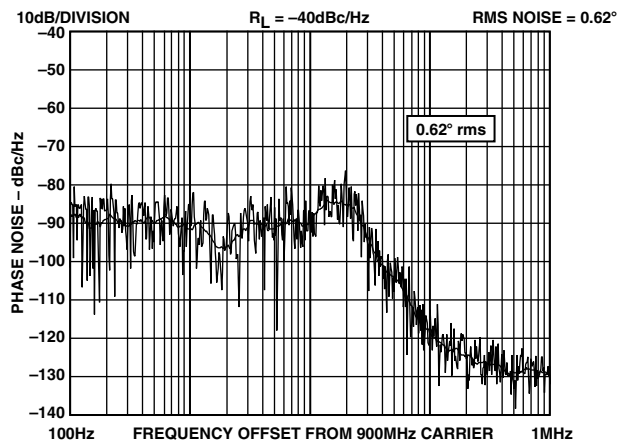
TPC 2. Input Sensitivity (ADF4113)



TPC 5. ADF4113 Integrated Phase Noise (900 MHz, 200 kHz, 20 kHz, Typical Lock Time: 400 μ s)

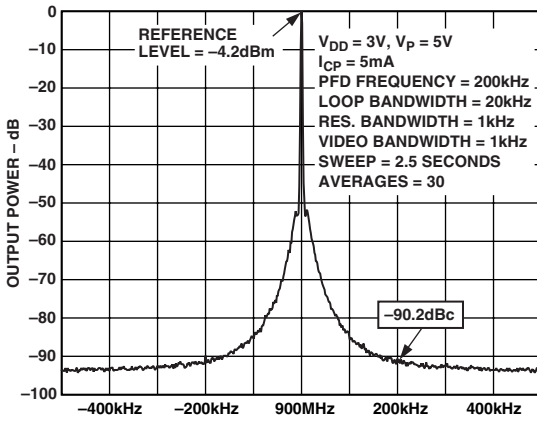


TPC 3. ADF4113 Phase Noise (900 MHz, 200 kHz, 20 kHz)

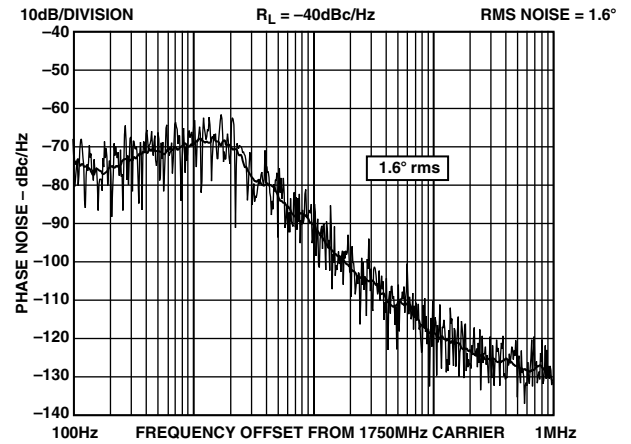


TPC 6. ADF4113 Integrated Phase Noise (900 MHz, 200 kHz, 35 kHz, Typical Lock Time: 200 μ s)

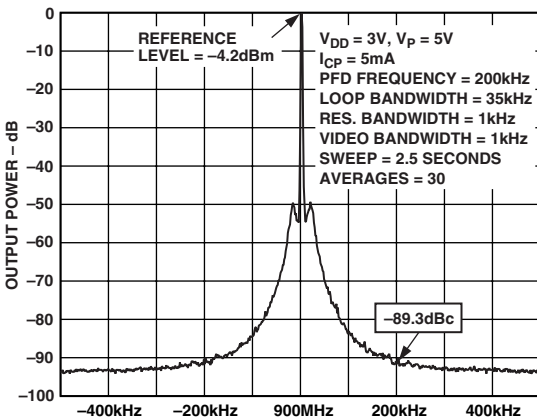
ADF4110/ADF4111/ADF4112/ADF4113



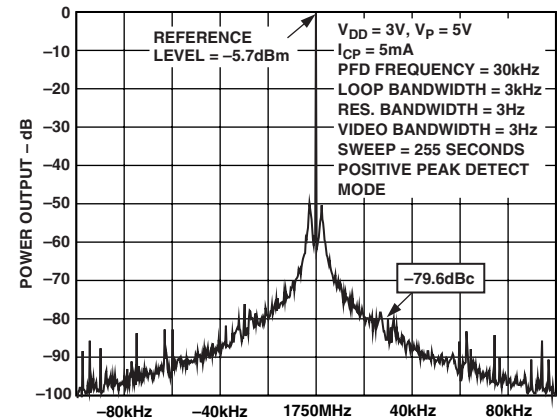
TPC 7. ADF4113 Reference Spurs (900 MHz, 200 kHz, 20 kHz)



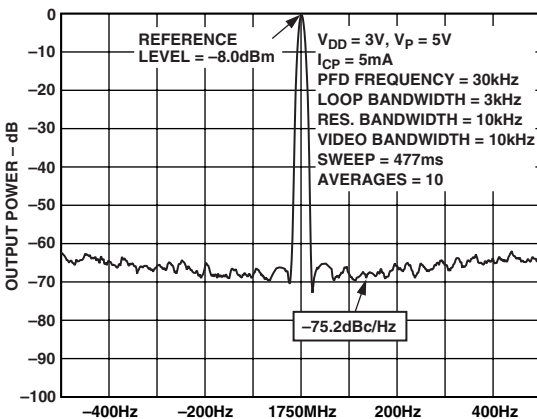
TPC 10. ADF4113 Integrated Phase Noise (1750 MHz, 30 kHz, 3 kHz)



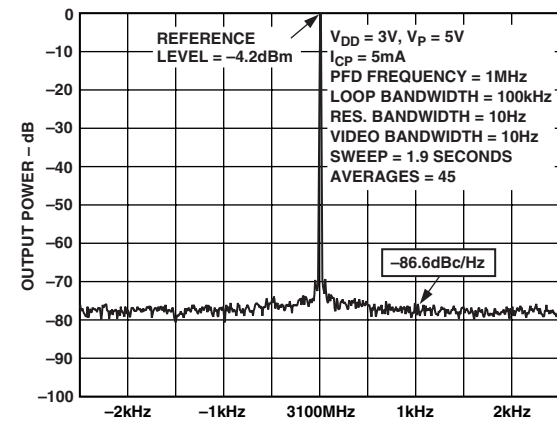
TPC 8. ADF4113 Reference Spurs (900 MHz, 200 kHz, 35 kHz)



TPC 11. ADF4113 Reference Spurs (1750 MHz, 30 kHz, 3 kHz)

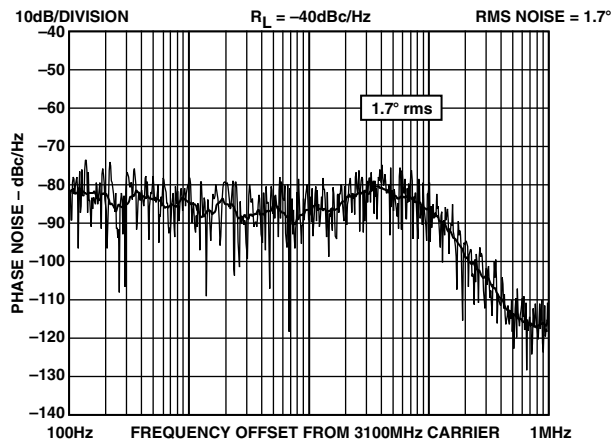


TPC 9. ADF4113 Phase Noise (1750 MHz, 30 kHz, 3 kHz)

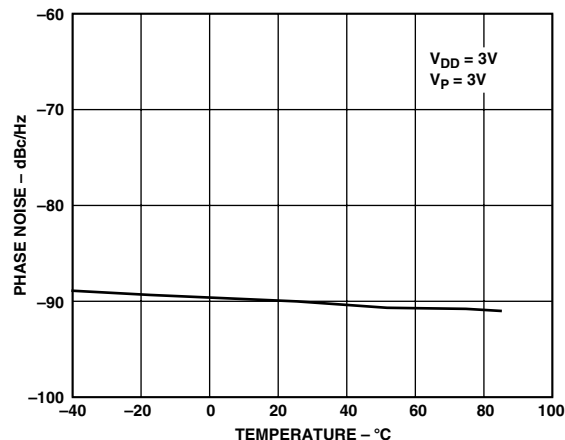


TPC 12. ADF4113 Phase Noise (3100 MHz, 1 MHz, 100 kHz)

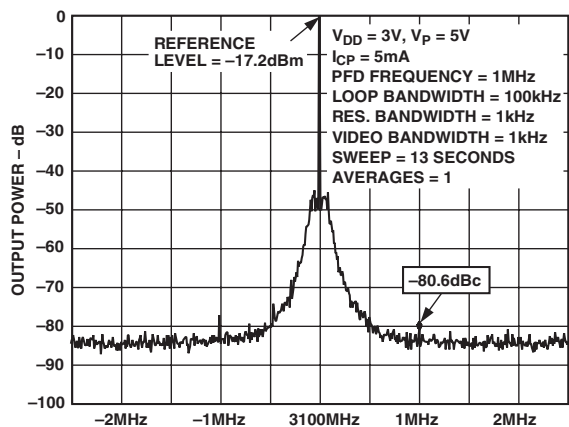
ADF4110/ADF4111/ADF4112/ADF4113



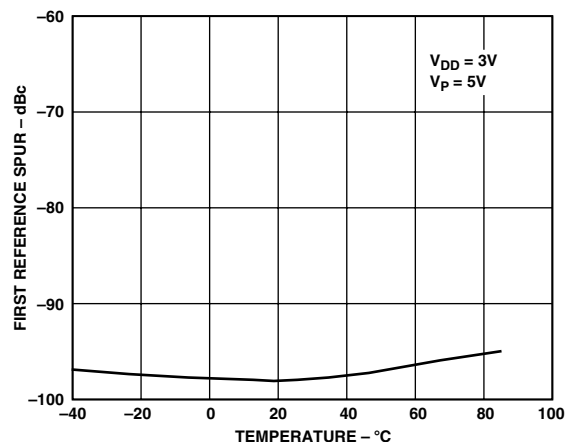
TPC 13. ADF4113 Integrated Phase Noise (3100 MHz, 1 MHz, 100 kHz)



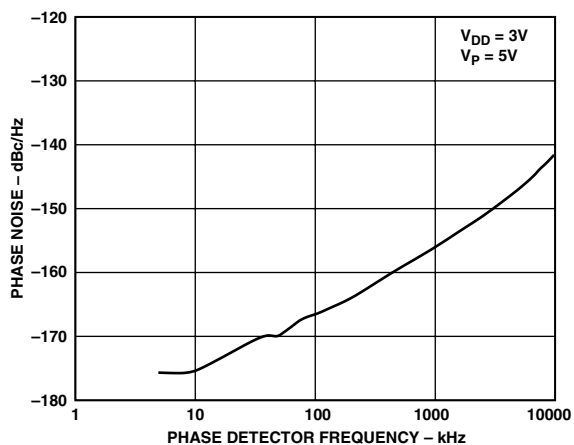
TPC 16. ADF4113 Phase Noise vs. Temperature (900 MHz, 200 kHz, 20 kHz)



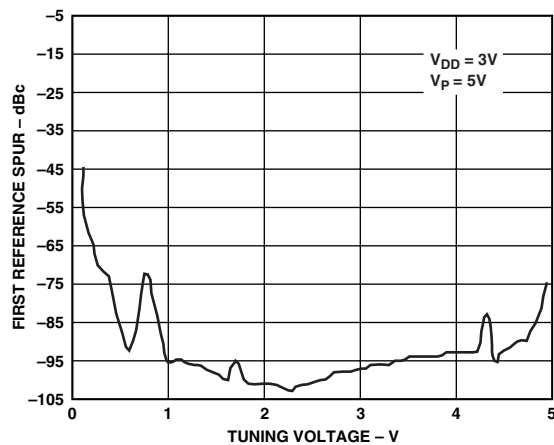
TPC 14. ADF4113 Reference Spurs (3100 MHz, 1 MHz, 100 kHz)



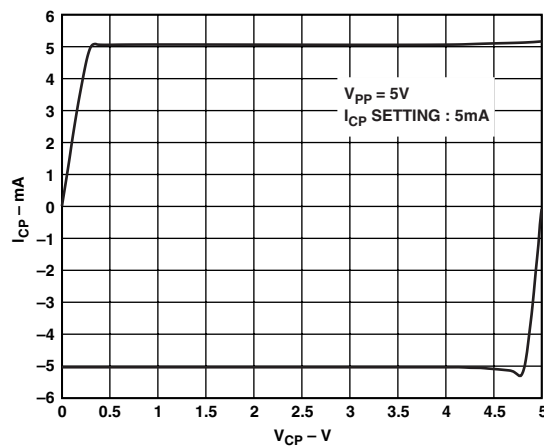
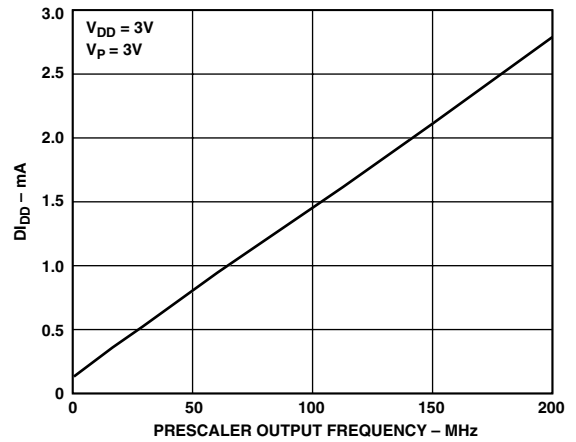
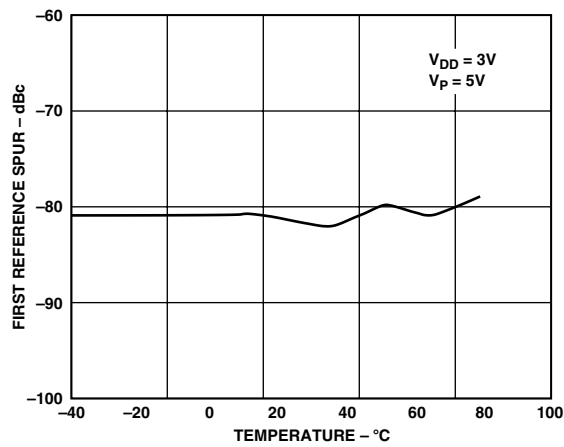
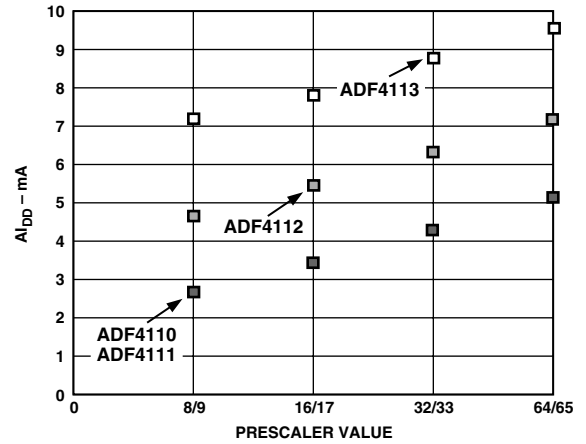
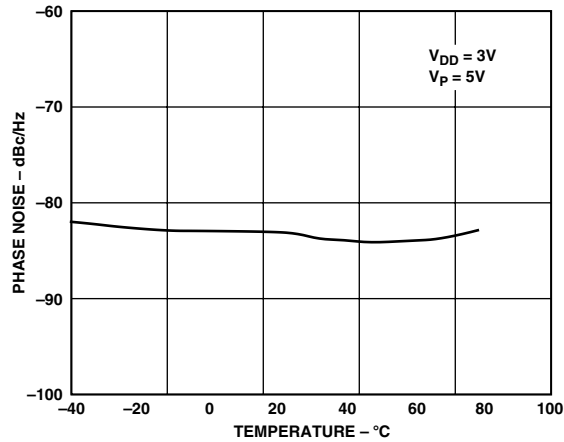
TPC 17. ADF4113 Reference Spurs vs. Temperature (900 MHz, 200 kHz, 20 kHz)



TPC 15. ADF4113 Phase Noise (Referred to CP Output) vs. PFD Frequency



TPC 18. ADF4113 Reference Spurs (200 kHz) vs. V_{TUNE} (900 MHz, 200 kHz, 20 kHz)



ADF4110/ADF4111/ADF4112/ADF4113

CIRCUIT DESCRIPTION

REFERENCE INPUT SECTION

The reference input stage is shown in Figure 2. SW1 and SW2 are normally closed switches. SW3 is normally open. When power-down is initiated, SW3 is closed and SW1 and SW2 are opened. This ensures that there is no loading of the REF_{IN} pin on power-down.

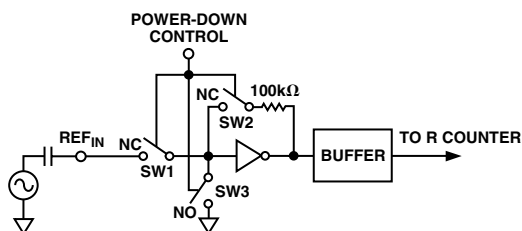


Figure 2. Reference Input Stage

RF INPUT STAGE

The RF input stage is shown in Figure 3. It is followed by a 2-stage limiting amplifier to generate the current mode logic (CML) clock levels needed for the prescaler.

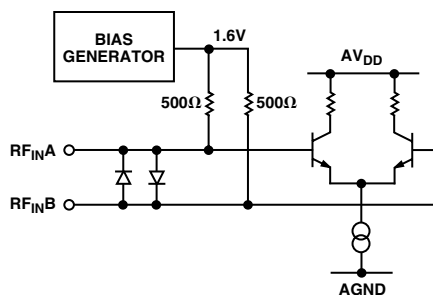


Figure 3. RF Input Stage

PRESALER (P/P+1)

The dual-modulus prescaler (P/P+1), along with the A and B counters, enables the large division ratio, N, to be realized ($N = BP + A$). The dual-modulus prescaler, operating at CML levels, takes the clock from the RF input stage and divides it down to a manageable frequency for the CMOS A and B counters. The prescaler is programmable. It can be set in software to 8/9, 16/17, 32/33, or 64/65. It is based on a synchronous 4/5 core.

A AND B COUNTERS

The A and B CMOS counters combine with the dual-modulus prescaler to allow a wide ranging division ratio in the PLL feedback counter. The counters are specified to work when the prescaler output is 200 MHz or less. Thus, with an RF input frequency of 2.5 GHz, a prescaler value of 16/17 is valid but a value of 8/9 is not valid.

Pulse Swallow Function

The A and B counters, in conjunction with the dual-modulus prescaler, make it possible to generate output frequencies that are spaced only by the reference frequency divided by R. The equation for the VCO frequency is as follows:

$$f_{VCO} = \left[(P \times B) + A \right] f_{REFIN} / R$$

f_{VCO} Output frequency of external voltage controlled oscillator (VCO)

P Preset modulus of dual-modulus prescaler

B Preset divide ratio of binary 13-bit counter (3 to 8191)

A Preset divide ratio of binary 6-bit swallow counter (0 to 63)

f_{REFIN} Output frequency of the external reference frequency oscillator

R Preset divide ratio of binary 14-bit programmable reference counter (1 to 16383)

R COUNTER

The 14-bit R counter allows the input reference frequency to be divided down to produce the reference clock to the phase frequency detector (PFD). Division ratios from 1 to 16,383 are allowed.

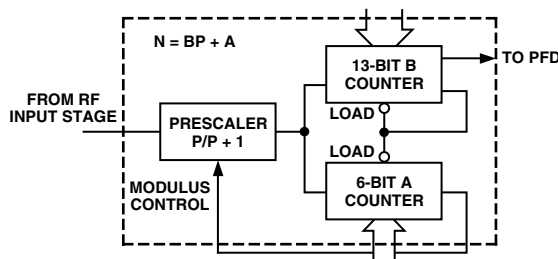


Figure 4. A and B Counters

PHASE FREQUENCY DETECTOR (PFD) AND CHARGE PUMP

The PFD takes inputs from the R counter and N counter ($N = BP + A$) and produces an output proportional to the phase and frequency difference between them. Figure 5 is a simplified schematic. The PFD includes a programmable delay element that controls the width of the antibacklash pulse. This pulse ensures that there is no dead zone in the PFD transfer function and minimizes phase noise and reference spurs. Two bits in the reference counter latch, ABP2 and ABP1, control the width of the pulse. See Table III.

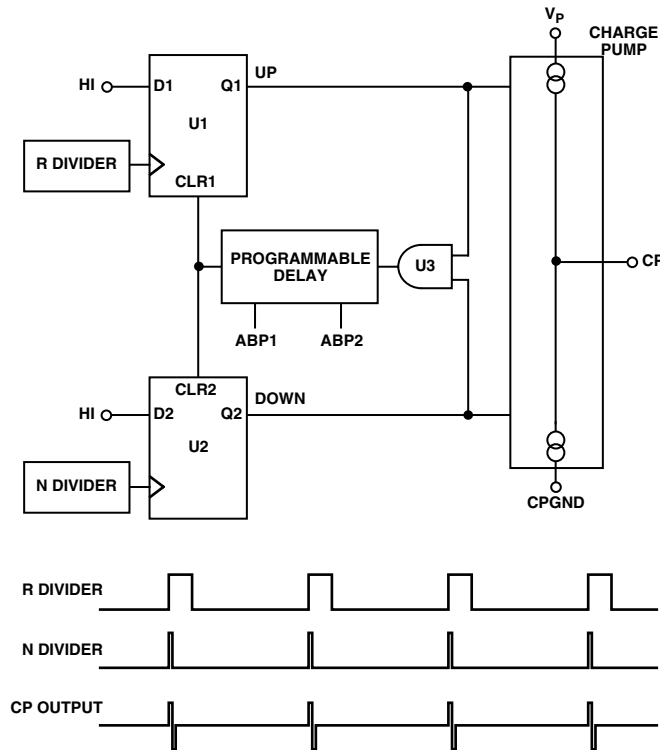


Figure 5. PFD Simplified Schematic and Timing (In Lock)

MUXOUT AND LOCK DETECT

The output multiplexer on the ADF4110 family allows the user to access various internal points on the chip. The state of MUXOUT is controlled by M3, M2, and M1 in the function latch. Table V shows the full truth table. Figure 6 shows the MUXOUT section in block diagram form.

Lock Detect

MUXOUT can be programmed for two types of lock detect: digital lock detect and analog lock detect.

Digital lock detect is active high. When LDP in the R counter latch is set to 0, digital lock detect is set high when the phase error on three consecutive phase detector (PD) cycles is less than 15 ns. With LDP set to 1, five consecutive cycles of less than 15 ns are required to set the lock detect. It will stay set high until a phase error of greater than 25 ns is detected on any subsequent PD cycle.

The N-channel open-drain analog lock detect should be operated with an external pull-up resistor of 10 k Ω nominal. When lock has been detected, this output will be high with narrow low-going pulses.

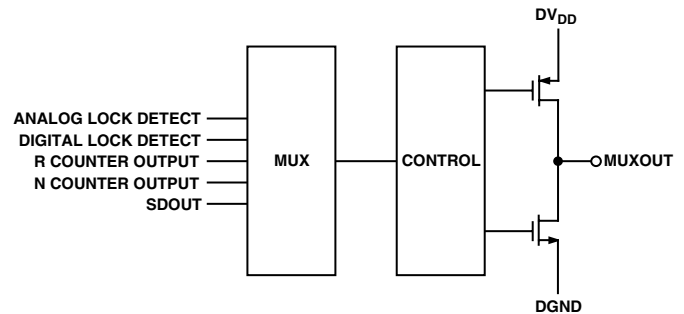


Figure 6. MUXOUT Circuit

INPUT SHIFT REGISTER

The ADF4110 family digital section includes a 24-bit input shift register, a 14-bit R counter, and a 19-bit N counter, comprising a 6-bit A counter and a 13-bit B counter. Data is clocked into the 24-bit shift register on each rising edge of CLK. The data is clocked in MSB first. Data is transferred from the shift register to one of four latches on the rising edge of LE. The destination latch is determined by the state of the two control bits (C2, C1) in the shift register. These are the two LSBs, DB1 and DB0, as shown in the timing diagram of Figure 1. The truth table for these bits is shown in Table I. Table II shows a summary of how the latches are programmed.

Table I. C2, C1 Truth Table

Control Bits		Data Latch
C2	C1	
0	0	R Counter
0	1	N Counter (A and B)
1	0	Function Latch (Including Prescaler)
1	1	Initialization Latch

ADF4110/ADF4111/ADF4112/ADF4113

Table II. ADF4110 Family Latch Summary

REFERENCE COUNTER LATCH

RESERVED	DLY	SYNC	LOCK DETECT PRECISION	TEST MODE BITS		ANTI- BACKLASH WIDTH		14-BIT REFERENCE COUNTER, R														CONTROL BITS	
DB23	DB22	DB21	DB20	DB19	DB18	DB17	DB16	DB15	DB14	DB13	DB12	DB11	DB10	DB9	DB8	DB7	DB6	DB5	DB4	DB3	DB2	DB1	DB0
X	DLY	SYNC	LDP	T2	T1	ABP2	ABP1	R14	R13	R12	R11	R10	R9	R8	R7	R6	R5	R4	R3	R2	R1	C2 (0)	C1 (0)

X = DON'T CARE

N COUNTER LATCH

RESERVED		CP GAIN	13-BIT B COUNTER													6-BIT A COUNTER						CONTROL BITS	
DB23	DB22	DB21	DB20	DB19	DB18	DB17	DB16	DB15	DB14	DB13	DB12	DB11	DB10	DB9	DB8	DB7	DB6	DB5	DB4	DB3	DB2	DB1	DB0
X	X	G1	B13	B12	B11	B10	B9	B8	B7	B6	B5	B4	B3	B2	B1	A6	A5	A4	A3	A2	A1	C2 (0)	C1 (1)

X = DON'T CARE

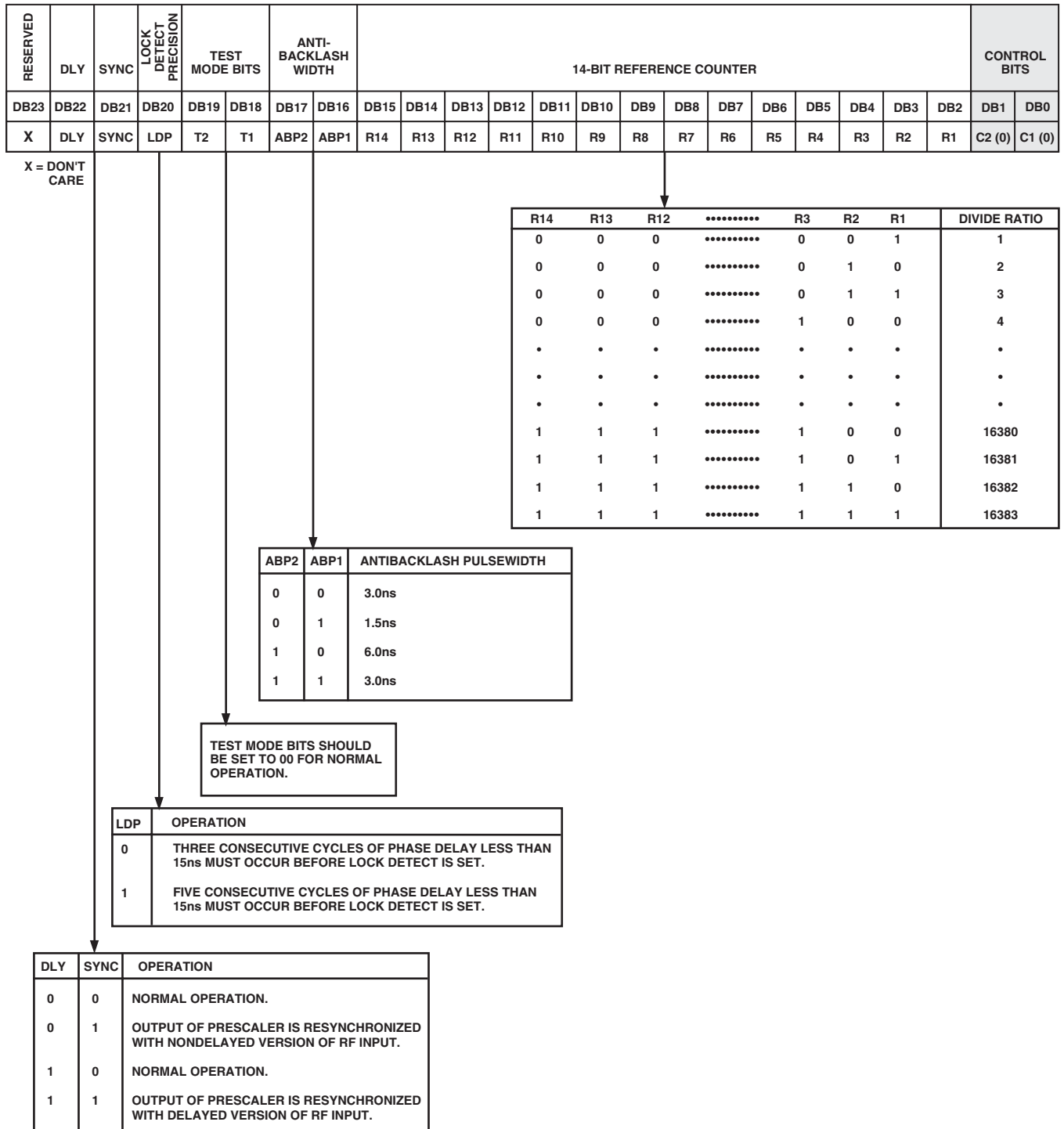
FUNCTION LATCH

PRESCALER VALUE		POWER- DOWN 2	CURRENT SETTING 2			CURRENT SETTING 1			TIMER COUNTER CONTROL				FASTLOCK MODE	FASTLOCK ENABLE	CP THREE- STATE	PD POLARITY	MUXOUT CONTROL			POWER- DOWN 1	COUNTER RESET	CONTROL BITS	
DB23	DB22	DB21	DB20	DB19	DB18	DB17	DB16	DB15	DB14	DB13	DB12	DB11	DB10	DB9	DB8	DB7	DB6	DB5	DB4	DB3	DB2	DB1	DB0
P2	P1	PD2	CPI6	CPI5	CPI4	CPI3	CPI2	CPI1	TC4	TC3	TC2	TC1	F5	F4	F3	F2	M3	M2	M1	PD1	F1	C2 (1)	C1 (0)

INITIALIZATION LATCH

PRESCALER VALUE		POWER- DOWN 2	CURRENT SETTING 2			CURRENT SETTING 1			TIMER COUNTER CONTROL				FASTLOCK MODE	FASTLOCK ENABLE	CP THREE- STATE	PD POLARITY	MUXOUT CONTROL			POWER- DOWN 1	COUNTER RESET	CONTROL BITS	
DB23	DB22	DB21	DB20	DB19	DB18	DB17	DB16	DB15	DB14	DB13	DB12	DB11	DB10	DB9	DB8	DB7	DB6	DB5	DB4	DB3	DB2	DB1	DB0
P2	P1	PD2	CPI6	CPI5	CPI4	CPI3	CPI2	CPI1	TC4	TC3	TC2	TC1	F5	F4	F3	F2	M3	M2	M1	PD1	F1	C2 (1)	C1 (1)

Table III. Reference Counter Latch Map



ADF4110/ADF4111/ADF4112/ADF4113

Table IV. AB Counter Latch Map

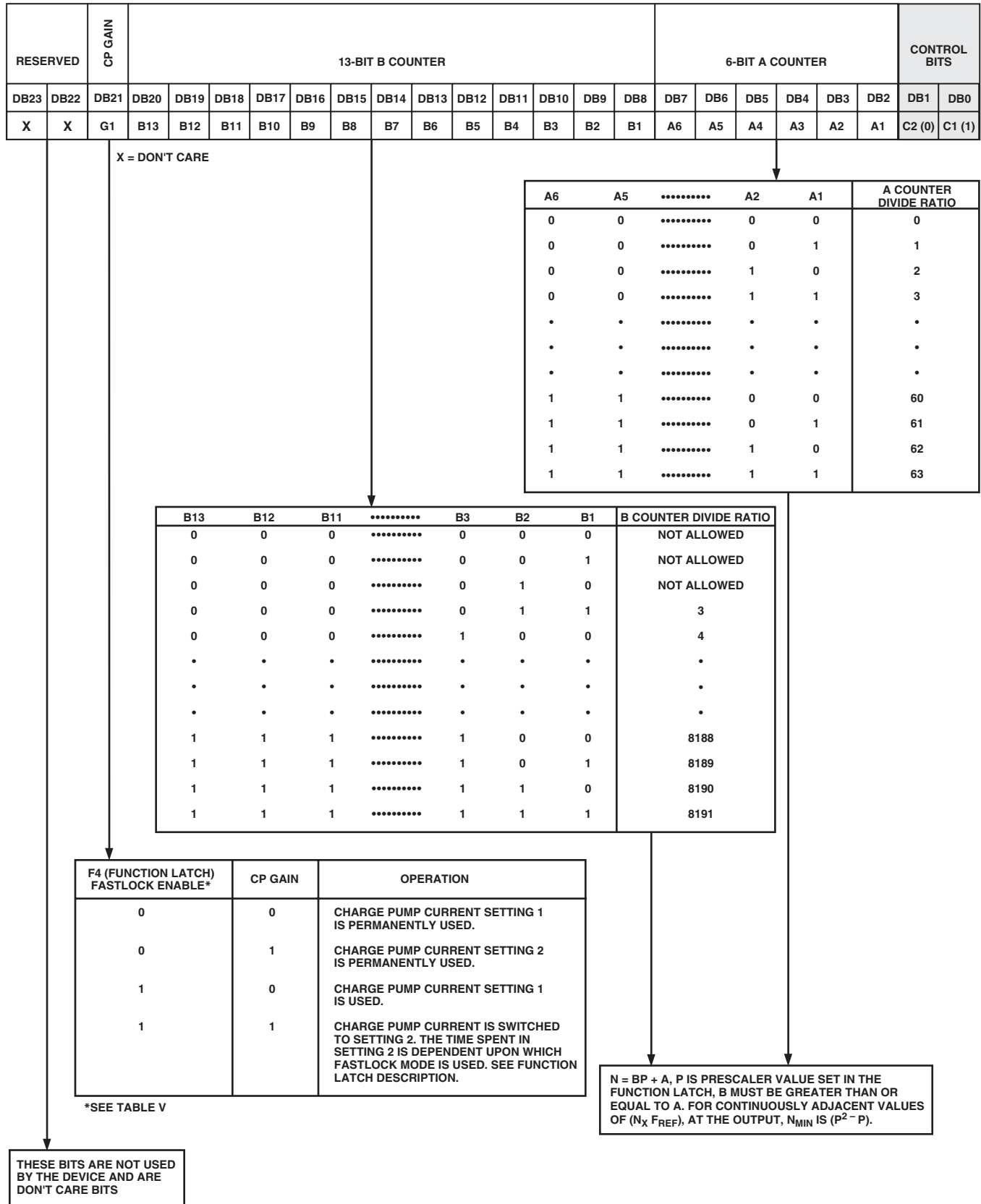
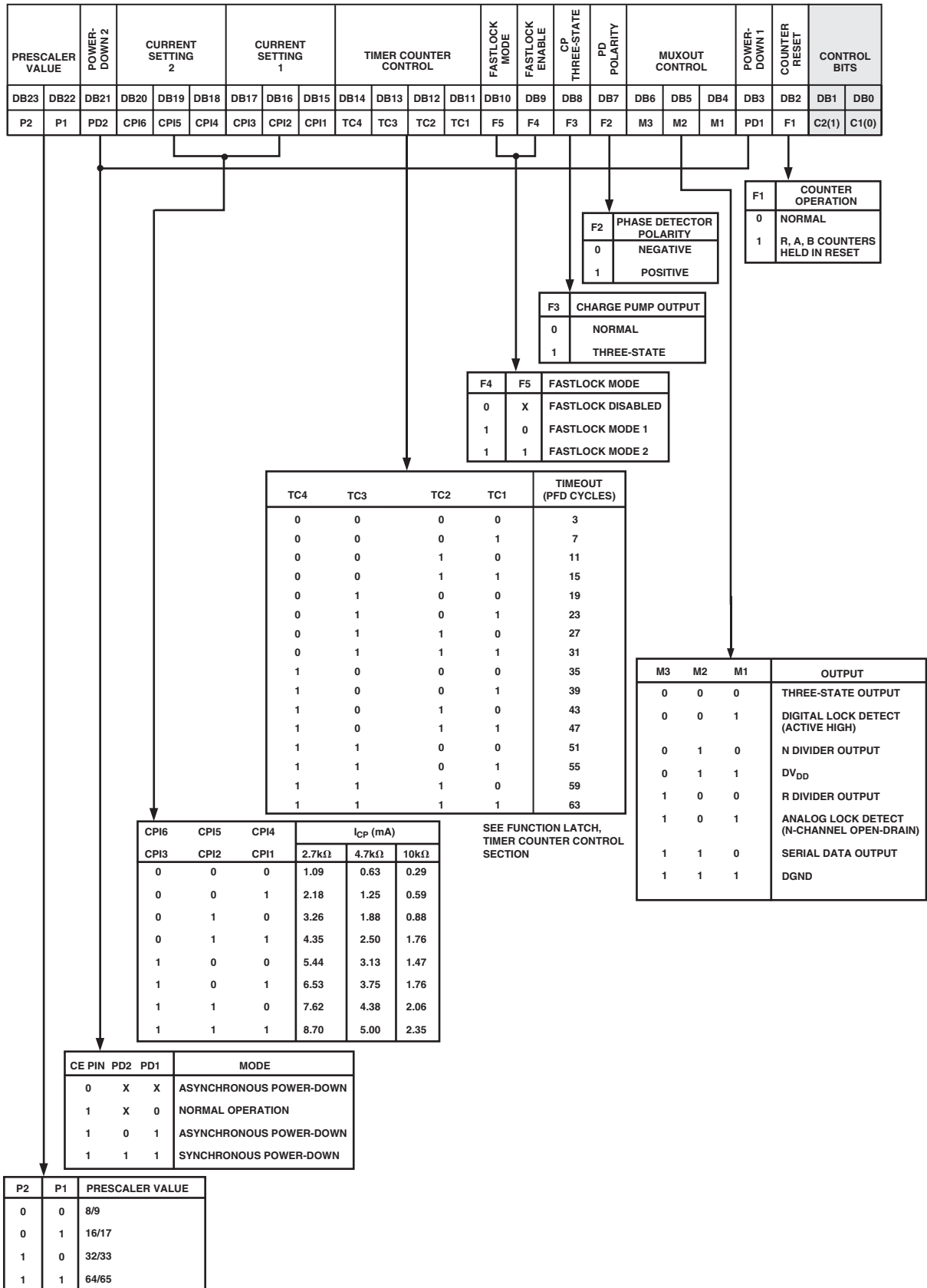
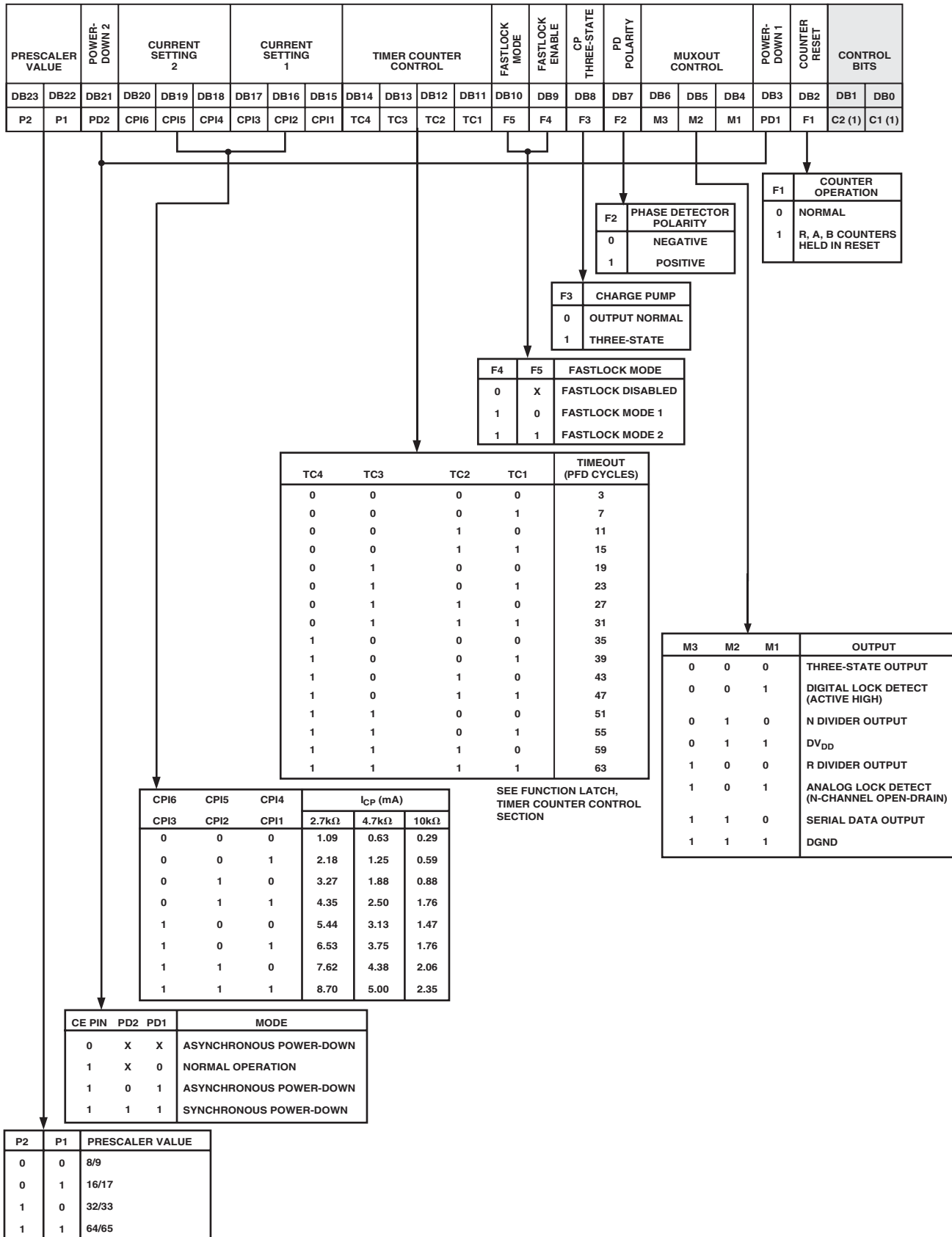


Table V. Function Latch Map



ADF4110/ADF4111/ADF4112/ADF4113

Table VI. Initialization Latch Map



FUNCTION LATCH

With C2, C1 set to 1, 0, the on-chip function latch will be programmed. Table V shows the input data format for programming the function latch.

Counter Reset

DB2 (F1) is the counter reset bit. When this is 1, the R counter and the AB counters are reset. For normal operation, this bit should be 0. *Upon powering up, the F1 bit needs to be disabled, the N counter resumes counting in “close” alignment with the R counter. (The maximum error is one prescaler cycle.)*

Power-Down

DB3 (PD1) and DB21 (PD2) on the ADF4110 family provide programmable power-down modes. They are enabled by the CE pin.

When the CE pin is low, the device is immediately disabled regardless of the states of PD2, PD1.

In the programmed asynchronous power-down, the device powers down immediately after latching a 1 into bit PD1, with the condition that PD2 has been loaded with a 0.

In the programmed synchronous power-down, the device power-down is gated by the charge pump to prevent unwanted frequency jumps. Once the power-down is enabled by writing a 1 into bit PD1 (on condition that a 1 has also been loaded to PD2), the device will go into power-down on the occurrence of the next charge pump event.

When a power-down is activated (either synchronous or asynchronous mode including CE-pin-activated power-down), the following events occur:

- All active dc current paths are removed.
- The R, N, and timeout counters are forced to their load state conditions.
- The charge pump is forced into three-state mode.
- The digital clock detect circuitry is reset.
- The RF_{IN} input is debiased.
- The reference input buffer circuitry is disabled.
- The input register remains active and capable of loading and latching data.

MUXOUT Control

The on-chip multiplexer is controlled by M3, M2, and M1 on the ADF4110 family. Table V shows the truth table.

Fastlock Enable Bit

DB9 of the function latch is the fastlock enable bit. Only when this is 1 is fastlock enabled.

Fastlock Mode Bit

DB10 of the function latch is the fastlock enable bit. When fastlock is enabled, this bit determines which fastlock mode is used. If the fastlock mode bit is 0, then fastlock mode 1 is selected and if the fastlock mode bit is 1, then Fastlock Mode 2 is selected.

Fastlock Mode 1

The charge pump current is switched to the contents of Current Setting 2.

The device enters fastlock by having a 1 written to the CP gain bit in the AB counter latch. The device exits fastlock by having a 0 written to the CP gain bit in the AB counter latch.

Fastlock Mode 2

The charge pump current is switched to the contents of Current Setting 2.

The device enters fastlock by having a 1 written to the CP gain bit in the AB counter latch. The device exits fastlock under the control of the timer counter. After the timeout period determined by the value in TC4 through TC1, the CP gain bit in the AB counter latch is automatically reset to 0 and the device reverts to normal mode instead of fastlock. See Table V for the timeout periods.

Timer Counter Control

The user has the option of programming two charge pump currents. The intent is that Current Setting 1 is used when the RF output is stable and the system is in a static state. Current Setting 2 is meant to be used when the system is dynamic and in a state of change (i.e., when a new output frequency is programmed).

The normal sequence of events is as follows:

The user initially decides what the preferred charge pump currents are going to be. For example, they may choose 2.5 mA as Current Setting 1 and 5 mA as Current Setting 2.

At the same time, they must also decide how long they want the secondary current to stay active before reverting to the primary current. This is controlled by the timer counter control bits DB14 through DB11 (TC4 through TC1) in the function latch. The truth table is given in Table V.

A user can program a new output frequency simply by programming the AB counter latch with new values for A and B. At the same time, the CP gain bit can be set to a 1, which sets the charge pump with the value in CPI6 through CPI4 for a period of time determined by TC4 through TC1. When this time is up, the charge pump current reverts to the value set by CPI3 through CPI1. At the same time, the CP gain bit in the AB counter latch is reset to 0 and is ready for the next time the user wishes to change the frequency again.

Note that there is an enable feature on the timer counter. It is enabled when Fastlock Mode 2 is chosen by setting the fastlock mode bit (DB10) in the function latch to 1.

Charge Pump Currents

CPI3, CPI2, and CPI1 program Current Setting 1 for the charge pump. CPI6, CPI5, and CPI4 program Current Setting 2 for the charge pump. The truth table is given in Table V.

Prescaler Value

P2 and P1 in the function latch set the prescaler values. The prescaler value should be chosen so that the prescaler output frequency is always less than or equal to 200 MHz. Thus, with an RF frequency of 2 GHz, a prescaler value of 16/17 is valid but a value of 8/9 is not.

PD Polarity

This bit sets the phase detector polarity bit. See Table V.

CP Three-State

This bit controls the CP output pin. With the bit set high, the CP output is put into three-state. With the bit set low, the CP output is enabled.

ADF4110/ADF4111/ADF4112/ADF4113

INITIALIZATION LATCH

When C2, C1 = 1, 1, the initialization latch is programmed. This is essentially the same as the function latch (programmed when C2, C1 = 1, 0).

However, when the initialization latch is programmed, an additional internal reset pulse is applied to the R and AB counters. This pulse ensures that the AB counter is at load point when the AB counter data is latched and the device will begin counting in close phase alignment.

If the latch is programmed for synchronous power-down (CE pin is high; PD1 bit is high; PD2 bit is low), the internal pulse also triggers this power-down. The prescaler reference and the oscillator input buffer are unaffected by the internal reset pulse, so close phase alignment is maintained when counting resumes.

When the first AB counter data is latched after initialization, the internal reset pulse is again activated. However, successive AB counter loads after this will not trigger the internal reset pulse.

DEVICE PROGRAMMING AFTER INITIAL POWER-UP

After initial power-up of the device, there are three ways to program the device.

Initialization Latch Method

Apply V_{DD} . Program the initialization latch (11 in 2 LSBs of input word). Make sure that F1 bit is programmed to 0. Then do an R load (00 in 2 LSBs). Then do an AB load (01 in 2 LSBs).

When the initialization latch is loaded, the following occurs:

1. The function latch contents are loaded.
2. An internal pulse resets the R, A, B, and timeout counters to load state conditions and also three-states the charge pump. Note that the prescaler bandgap reference and the oscillator input buffer are unaffected by the internal reset pulse, allowing close phase alignment when counting resumes.
3. Latching the first AB counter data after the initialization word will activate the same internal reset pulse. Successive AB loads will not trigger the internal reset pulse unless there is another initialization.

CE Pin Method

Apply V_{DD} .

Bring CE low to put the device into power-down. This is an asynchronous power-down in that it happens immediately.

Program the function latch (10). Program the R counter latch (00). Program the AB counter latch (01).

Bring CE high to take the device out of power-down. The R and AB counters will now resume counting in close alignment.

Note that after CE goes high, a duration of 1 μ s may be required for the prescaler bandgap voltage and oscillator input buffer bias to reach steady state.

CE can be used to power the device up and down in order to check for channel activity. The input register does not need to be reprogrammed each time the device is disabled and enabled as long as it has been programmed at least once after V_{DD} was initially applied.

Counter Reset Method

Apply V_{DD} .

Do a function latch load (10 in 2 LSBs). As part of this, load 1 to the F1 bit. This enables the counter reset.

Do an R counter load (00 in 2 LSBs). Do an AB counter load (01 in 2 LSBs). Do a function latch load (10 in 2 LSBs). As part of this, load 0 to the F1 bit. This disables the counter reset.

This sequence provides the same close alignment as the initialization method. It offers direct control over the internal reset. Note that counter reset holds the counters at load point and three-states the charge pump but does not trigger synchronous power-down. The counter reset method requires an extra function latch load compared to the initialization latch method.

RESYNCHRONIZING THE PRESCALER OUTPUT

Table III (the Reference Counter Latch Map) shows two bits, DB22 and DB21, which are labelled DLY and SYNC, respectively. These bits affect the operation of the prescaler.

With SYNC = 1, the prescaler output is resynchronized with the RF input. This has the effect of reducing jitter due to the prescaler and can lead to an overall improvement in synthesizer phase noise performance. Typically, a 1 dB to 2 dB improvement is seen in the ADF4113. The lower bandwidth devices can show an even greater improvement. For example, the ADF4110 phase noise is typically improved by 3 dB when SYNC is enabled.

With DLY = 1, the prescaler output is resynchronized with a delayed version of the RF input.

If the SYNC feature is used on the synthesizer, some care must be taken. At some point, (at certain temperatures and output frequencies), the delay through the prescaler will coincide with the active edge on RF input and this will cause the SYNC feature to break down. So, it is important when using the SYNC feature to be aware of this. Adding a delay to the RF signal, by programming DLY = 1, will extend the operating frequency and temperature somewhat. Using the SYNC feature will also increase the value of the AI_{DD} for the device. With a 900 MHz output, the ADF4113 AI_{DD} increases by about 1.3 mA when SYNC is enabled and an additional 0.3 mA if DLY is enabled.

All the typical performance plots on the data sheet except for TPC 4 apply for DLY and SYNC = 0, i.e., no resynchronization or delay enabled.

ADF4110/ADF4111/ADF4112/ADF4113

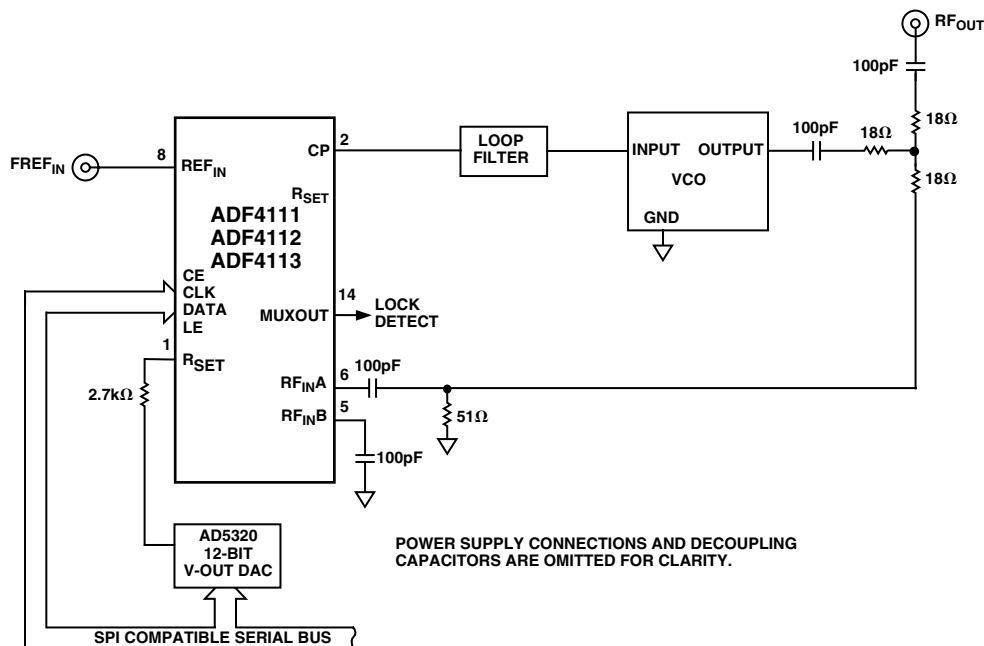


Figure 8. Driving the R_{SET} Pin with a D/A Converter

USING A D/A CONVERTER TO DRIVE THE R_{SET} PIN

You can use a D/A converter to drive the R_{SET} pin of the ADF4110 family and thus increase the level of control over the charge pump current I_{CP} . This can be advantageous in wideband applications where the sensitivity of the VCO varies over the tuning range. To compensate for this, the I_{CP} may be varied to maintain good phase margin and ensure loop stability. See Figure 8.

SHUTDOWN CIRCUIT

The attached circuit in Figure 9 shows how to shut down both the ADF4110 family and the accompanying VCO. The ADG701 switch goes closed circuit when a Logic 1 is applied to the IN input. The low cost switch is available in both SOT-23 and micro SO packages.

WIDEBAND PLL

Many of the wireless applications for synthesizers and VCOs in PLLs are narrowband in nature. These applications include the various wireless standards like GSM, DSC1800, CDMA, and WCDMA. In each of these cases, the total tuning range for the local oscillator is less than 100 MHz. However, there are also wideband applications for which the local oscillator could have a

tuning range as wide as an octave. For example, cable TV tuners have a total range of about 400 MHz. Figure 10 shows an application where the ADF4113 is used to control and program the Micronetics M3500-2235. The loop filter was designed for an RF output of 2900 MHz, a loop bandwidth of 40 kHz, a PFD frequency of 1 MHz, I_{CP} of 10 mA (2.5 mA synthesizer I_{CP} multiplied by the gain factor of 4), VCO K_D of 90 MHz/V (sensitivity of the M3500-2235 at an output of 2900 MHz), and a phase margin of 45°C.

In narrow-band applications, there is generally a small variation in output frequency (generally less than 10%) and a small variation in VCO sensitivity over the range (typically 10% to 15%). However, in wideband applications both of these parameters have a much greater variation. In Figure 10, for example, there is a -25% and +17% variation in the RF output from the nominal 2.9 GHz. The sensitivity of the VCO can vary from 120 MHz/V at 2750 MHz to 75 MHz/V at 3400 MHz (+33%, -17%). Variations in these parameters will change the loop bandwidth. This in turn can affect stability and lock time. By changing the programmable I_{CP} , it is possible to get compensation for these varying loop conditions and ensure that the loop is always operating close to optimal conditions.

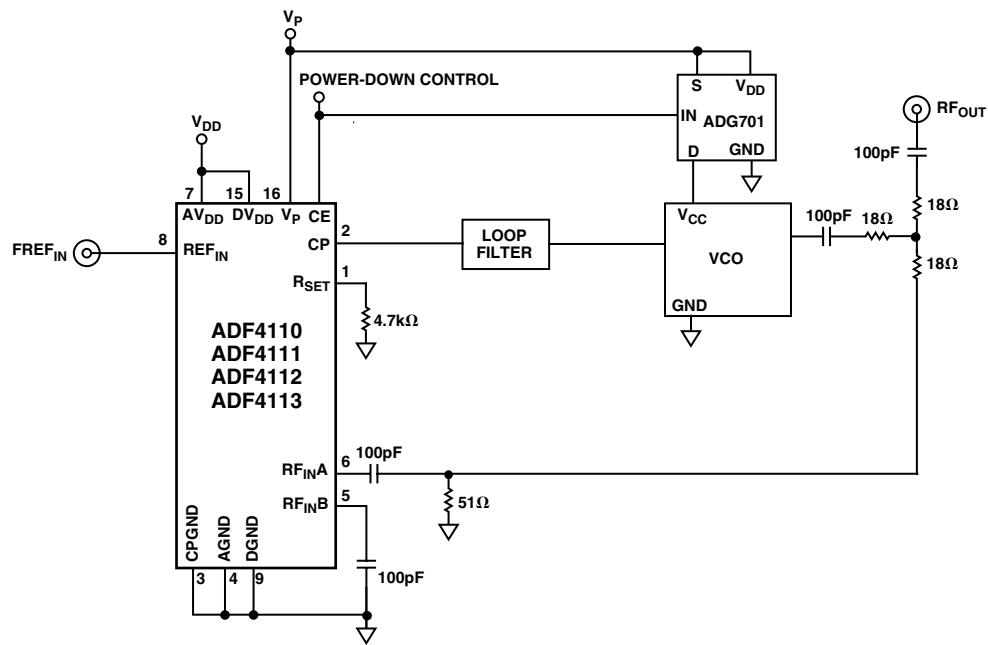


Figure 9. Local Oscillator Shutdown Circuit

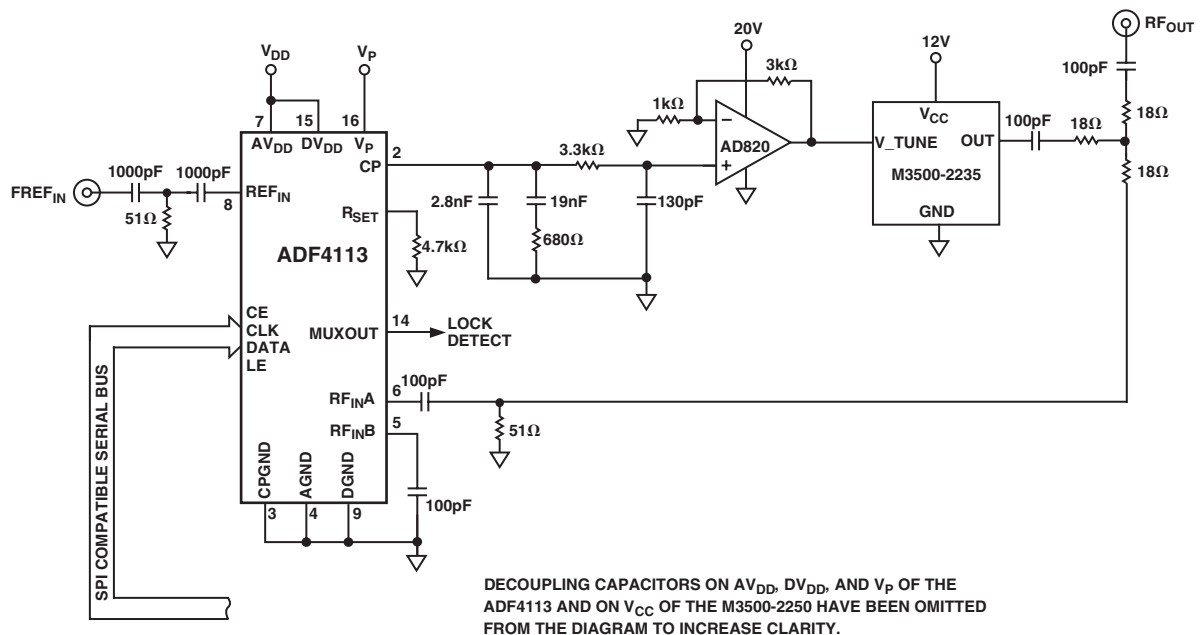


Figure 10. Wideband Phase-Locked Loop

ADF4110/ADF4111/ADF4112/ADF4113

DIRECT CONVERSION MODULATOR

In some applications a direct conversion architecture can be used in base station transmitters. Figure 11 shows the combination available from ADI to implement this solution.

The circuit diagram shows the AD9761 being used with the AD8346. The use of dual integrated DACs such as the AD9761 with specified ± 0.02 dB and ± 0.004 dB gain and offset matching characteristics ensures minimum error contribution (over temperature) from this portion of the signal chain.

The local oscillator (LO) is implemented using the ADF4113. In this case, the OSC 3B1-13M0 provides the stable 13 MHz reference frequency. The system is designed for a 200 kHz channel spacing and an output center frequency of 1960 MHz.

The target application is a WCDMA base station transmitter. Typical phase noise performance from this LO is -85 dBc/Hz at a 1 kHz offset.

The LO port of the AD8346 is driven in single-ended fashion. LOIN is ac-coupled to ground with the 100 pF capacitor and LOIP is driven through the ac coupling capacitor from a 50 Ω source. An LO drive level of between -6 dBm and -12 dBm is required. The circuit of Figure 11 gives a typical level of -8 dBm.

The RF output is designed to drive a 50 Ω load but must be ac-coupled as shown in Figure 11. If the I and Q inputs are driven in quadrature by 2 V p-p signals, the resulting output power will be around -10 dBm.

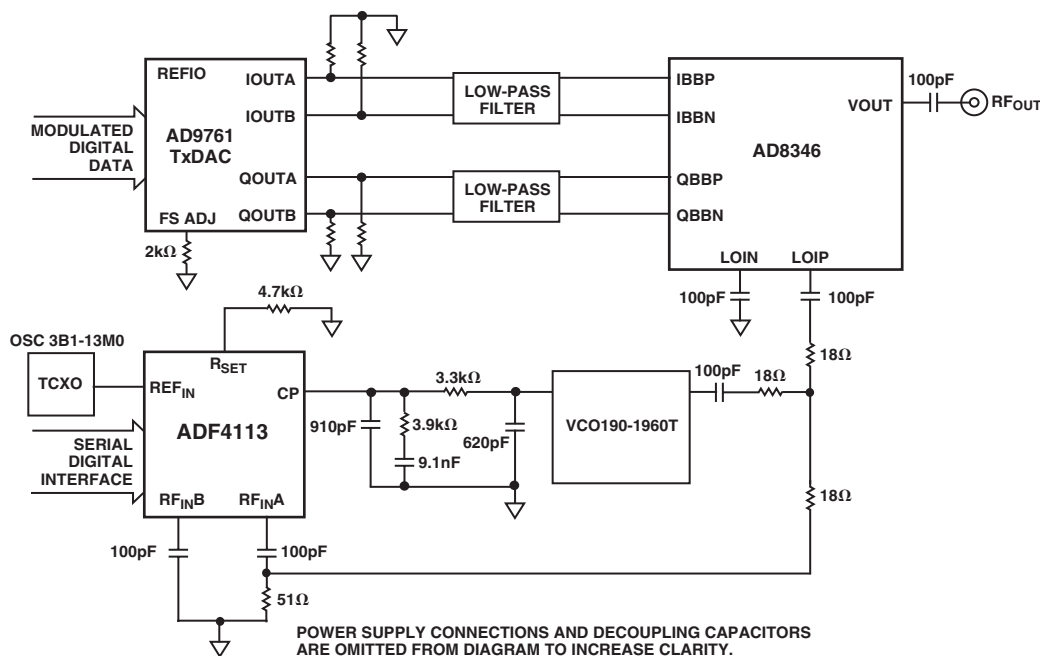


Figure 11. Direct Conversion Transmitter Solution

INTERFACING

The ADF4110 family has a simple SPI® compatible serial interface for writing to the device. SCLK, SDATA, and LE control the data transfer. When latch enable (LE) goes high, the 24 bits that have been clocked into the input register on each rising edge of SCLK will get transferred to the appropriate latch. See Figure 1 for the Timing Diagram and Table I for the Latch Truth Table.

The maximum allowable serial clock rate is 20 MHz. This means that the maximum update rate possible for the device is 833 kHz or one update every 1.2 microseconds. This is certainly more than adequate for systems that will have typical lock times in hundreds of microseconds.

ADuC812 Interface

Figure 12 shows the interface between the ADF4110 family and the ADuC812 microconverter. Since the ADuC812 is based on an 8051 core, this interface can be used with any 8051 based microcontroller. The microconverter is set up for SPI Master Mode with CPHA = 0. To initiate the operation, the I/O port driving LE is brought low. Each latch of the ADF4110 family needs a 24-bit word. This is accomplished by writing three 8-bit bytes from the microconverter to the device. When the third byte has been written, the LE input should be brought high to complete the transfer.

When power is first applied to the ADF4110 family, three writes are needed (one each to the R counter latch, the N counter latch, and the initialization latch) for the output to become active.

I/O port lines on the ADuC812 are also used to control power-down (CE input) and to detect lock (MUXOUT configured as lock detect and polled by the port input).

When the ADuC812 is operating in the mode described above, the maximum SCLOCK rate of the ADuC812 is 4 MHz. This means that the maximum rate at which the output frequency can be changed will be 166 kHz.

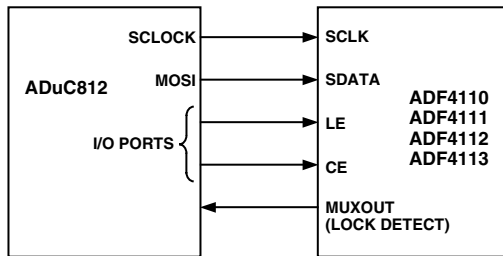


Figure 12. ADuC812 to ADF4110 Family Interface

ADSP-2181 Interface

Figure 13 shows the interface between the ADF4110 family and the ADSP-21xx digital signal processor. The ADF4110 family needs a 24-bit serial word for each latch write. The easiest way to accomplish this using the ADSP-21xx family is to use the autobuffered transmit mode of operation with alternate framing. This provides a means for transmitting an entire block of serial data before an interrupt is generated.

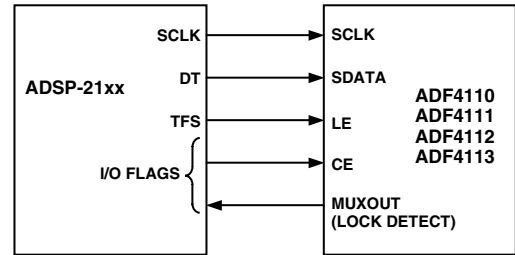


Figure 13. ADSP-21xx to ADF4110 Family Interface

Set up the word length for 8 bits and use three memory locations for each 24-bit word. To program each 24-bit latch, store the three 8-bit bytes, enable the autobuffered mode, and then write to the transmit register of the DSP. This last operation initiates the autobuffer transfer.

PCB DESIGN GUIDELINES FOR CHIP SCALE PACKAGE

The lands on the chip scale package (CP-20) are rectangular. The printed circuit board pad for these should be 0.1 mm longer than the package land length and 0.05 mm wider than the package land width. The land should be centered on the pad. This will ensure that the solder joint size is maximized.

The bottom of the chip scale package has a central thermal pad. The thermal pad on the printed circuit board should be at least as large as this exposed pad. On the printed circuit board, there should be a clearance of at least 0.25 mm between the thermal pad and the inner edges of the pad pattern. This will ensure that shorting is avoided.

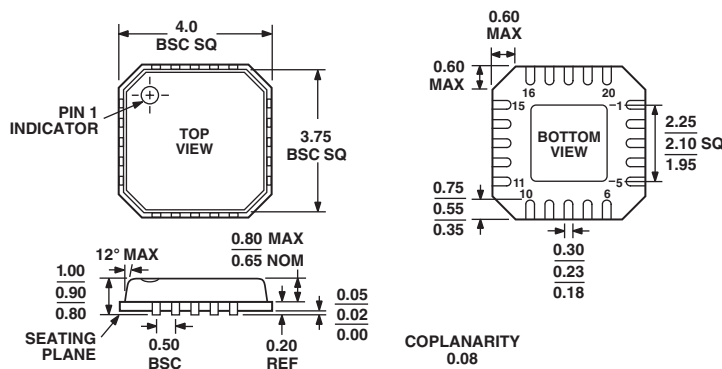
Thermal vias may be used on the printed circuit board thermal pad to improve thermal performance of the package. If vias are used, they should be incorporated in the thermal pad at 1.2 mm pitch grid. The via diameter should be between 0.3 mm and 0.33 mm and the via barrel should be plated with 1 oz. copper to plug the via.

The user should connect the printed circuit board thermal pad to AGND.

ADF4110/ADF4111/ADF4112/ADF4113

OUTLINE DIMENSIONS
20-Lead Lead Frame Chip Scale Package [LFCSP]
(CP-20)

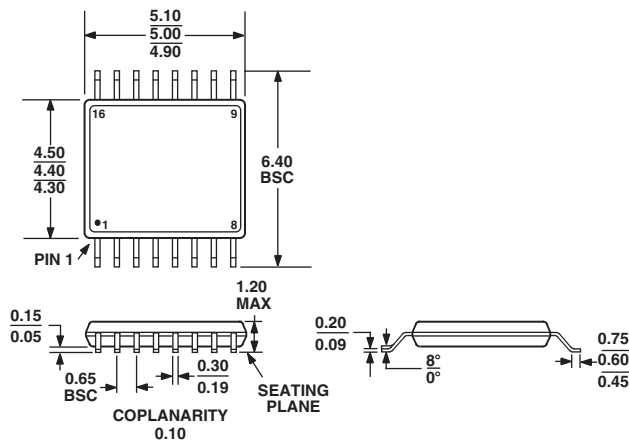
Dimensions shown in millimeters



COMPLIANT TO JEDEC STANDARDS MO-220-VGGD-1

16-Lead Thin Shrink Small Outline Package [TSSOP]
(RU-16)

Dimensions shown in millimeters



COMPLIANT TO JEDEC STANDARDS MO-153AB

Revision History

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Updated OUTLINE DIMENSIONS	24
1/01—Data Sheet changed from REV. 0 to REV. A.	
Changes to DC Specifications in B Version, B Chips, Unit and Test Conditions/Comments columns	2
Changes to Absolute Maximum Ratings	4
Change to RFINA Function text	5
Changes to Figure 8	7
New graph added—TPC 22	9
Change to PD Polarity Box in Table V	15
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Addition of new material (PCB Design Guidelines for Chip-Scale Package)	23
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